

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

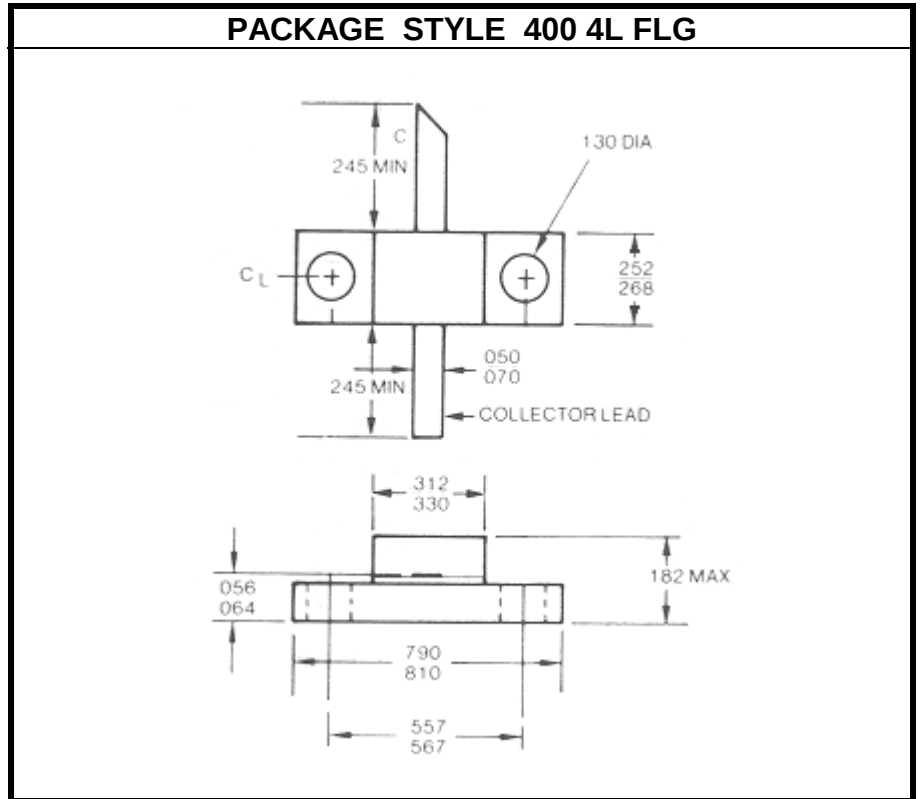
The **ASI MRAL1720-9** is Designed for Class C, Common Base Wideband Large Signal Amplifier Applications up to 2.0 GHz.

FEATURES:

- Diffused Ballast Resistors.
- Internal Matching Network
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A (CONT)
V_{CES}	42 V
V_{EBO}	3.5 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	4.5 °C/W



CHARACTERISTICS $T_C = 25\text{ °C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 80\text{ mA}$	42			V
BV_{EBO}	$I_E = 1.0\text{ mA}$	3.5			V
I_{CBO}	$V_{CB} = 22\text{ V}$			2.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 400\text{ mA}$	10		100	---
C_{ob}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$			12	pF
G_{PB}	$V_{CE} = 22\text{ V}$ $P_{out} = 9.0\text{ W}$ $f = 1.7\text{ GHz \& } 2.0\text{ GHz}$	6.5			dB
η_C		40			%